NSN 5961-01-342-5075

Semiconductor Device Set - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-342-5075
Inclosure Material:
Metal all transistor
Overall Length:
39.69 millimeters all transistor
Overall Height:
3.42 millimeters all transistor
Overall Width:
26.66 millimeters all transistor
Mounting Facility Quantity:
2 all transistor
Internal Configuration:
Junction contact all transistor
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-204aa all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
4 transistor
Mounting Method:
Unthreaded hole all transistor
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
400.0 breakdown voltage, collector-to-emitter, base open all transistor
Current Rating Per Characteristic:
15.00 amperes source cutoff current all transistor
Power Rating Per Characteristic:
175.0 watts small-signal input power, common-collector absolute all transistor
Transfer Ratio:
8.0 static forward current transfer ratio, common-emitter all transistor and 20.0 static forward current transfer ratio, common-emitter all
transistor
Maximum Operating Tempurature Per Measurement Point:
175.0 degrees celsius junction all transistor
Terminal Type And Quantity:
2 pin all transistor and 1 case all transistor
Shelf Life:
N/a

Unit Of Measure:

NSN 5961-01-342-5075

Semiconductor Device Set - Page 2 of 2



Demilitarization:

No

Fiig:

A110a0